PATENT COOPERATION TREATY

From the INTERNATIONAL SEARCHING AUTHORITY					
To: SEMICONDUCTOR ENERGY LABORATORY CO., LTD. 398, Hase, Atsugi-shi, Kanagawa 2430036 Japan	PCT WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43bis.1)				
	Date of mailing (day/month/year)	07.12.2004			
Applicant's or agent's file reference	FOR FURTHER A	CTION			
00000PCT7465		See paragraph 2 below			
International application No. PCT/JP2004/016183 International filing date 25.10		Priority date (day/month/year) 28.10.2003			
23.20	· · · · · · · · · · · · · · · · · · ·	28.10.2003			
International Patent Classification (IPC) or both national classific Int.Cl 7 HOLL 29/786, HOLL 21/336, HOLL 21/76 Applicant	8, H01L 21/288,				
SEMICONDUCTOR ENERGY LABO	RATORY CO	., LTD.			
Box No. VI Certain documents cited Box No. VI Certain defects in the international app	(a)(i) with regard to nov such statement olication	ve step and industrial applicability relty, inventive step or industrial applicability;			
Box No. VIII Certain observations on the internation	ai application	•			
 FURTHER ACTION If a demand for international preliminary examination is ma International Preliminary Examining Authority ("IPEA") exception of the than this one to be the IPEA and the chosen IPEA has nopinions of this International Searching Authority will not be If this opinion is, as provided above, considered to be a written a written reply together, where appropriate, with amendments, PCT/ISA/220 or before the expiration of 22 months from the preformation of the prefore of the preformation of the preformation of the preformation of	pt that this does not ap otified the Internation e so considered. opinion of the IPEA, before the expiration of	ply where the applicant chooses an Authority al Bureau under Rule 66.1bis(b) that written the applicant is invited to submit to the IPEA of 3 months from the date of mailing of Form			
	A .1				
Name and mailing address of the ISA/JP	Authorized officer	4M 3123			
Japan Patent Office 3-4-3 Kasumigaseki Chivoda-ku Tokyo 100-8915 Japan		Miyazaki			

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2004/016183

Во	x No. I	Basis of tl	he opinion								
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WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2004/ 016183

Box No. V Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

1.	Stat	em	ent
1.	Stat	em	ent

Novelty (N)	Claims	3-4,7,9,11-14		YES
	Claims	1-2,5-6,8,10	i	NO
Inventive step (IS)	Claims	12		_ YES
	Claims	1-11,13-14		_ NO
Industrial applicability (IA)	Claims	1-14		YES
	Claims			_ NO Î

2. Citations and explanations

D1:JP 2003-98548 A(HITACHI, LTD.,)

2003.04.03, whole document, Figs. 1-7

D2:JP 2002-49333 A(SEMICONDUCTOR ENERGY LABORATORY CO., LTD.)

2002.02.15, whole document, Figs.1-21

D3:JP 2003-506886 A(PATTERNING TECHNOLOGY LIMITED)

2003.02.18, whole document, Figs.1-27

D4:WO 1997/043689 A1(SEIKO EPSON CORPORATION)

1997.11.20,page27-28, Figs.14-16

D5:JP 7-297404 A(KABUSHIKI KAISHA TOSHIBA)

1995.11.10, whole document, Figs. 1-6

D6:JP 4-56168 A(STANLEY ELECTRIC CO., LTD.)

1992.02.24, whole document, Fig.1

[Claims 1-2,5-6,8,10]

The subject matter of claims 1-2,5-6,8,10 does not appear to be novel and to involve an inventive step with respect to the cited document D1.

The subject matter of claims 1-2,5-6,8,10 is disclosed in the cited document D1.

[Claims 3-4,7,9]

The subject matter of claims 3-4,7,9 does not appear to involve an inventive step in view of the cited documents D1- D2.

D2 discloses that a driver circuit is constructed by a second thin film transistor which comprises the same layer structure of a first thin film transistor and the driver circuit comprises only n-channel type thin film transistor.

[Claims 11]

The subject matter of claim 11 does not appear to involve an inventive step in view of the cited documents D1- D4.

D3-D4 disclose a mask is formed by a droplet discharge method.

[Claims 12]

The subject matter of claim 12 is neither disclosed in any of the documents cited in the ISR nor obvious to a person skilled in the art.

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2004/016183

Supplemental Box

In case the space in any of the preceding boxes is not sufficient.

Continuation of: Box No.V

[Claims 13]

The subject matter of claim 13 does not appear to involve an inventive step in view of the cited documents D1- D5.

D5 discloses the step of laminating a gate insulating layer, a semiconductor layer, and an insulating layer over the gate electrode is carried out without exposing to the atmosphere.

[Claims 14]

The subject matter of claim 14 does not appear to involve an inventive step in view of the cited documents D1- D6.

D6 discloses the gate insulating film is sequentially laminated by a first silicon nitride film, a silicon oxide film, and a second silicon nitride film.